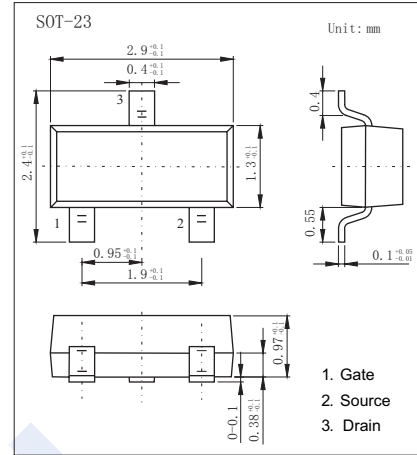


P-Channel MOSFET

KI009P

■ Features

- $V_{DS} (V) = -12V$
- $I_D = -4 A$
- $R_{DS(ON)} < 52m\Omega$ ($V_{GS} = -4.5V$, $I_D = -4A$)
- $R_{DS(ON)} < 87m\Omega$ ($V_{GS} = -2.5V$, $I_D = -3A$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-12	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current	I_D	4	A
Power Dissipation	P_D	1	W
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{BSS}	$I_D = -250 \mu A$, $V_{GS} = 0V$	-12			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -12V$, $V_{GS} = 0V$			-1	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0V$, $V_{GS} = \pm 12V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	-0.4		-1	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5V$, $I_D = -4A$		45	52	$m\Omega$
		$V_{GS} = -2.5V$, $I_D = -3A$		65	87	
Diode Forward Voltage	V_{SD}	$I_S = -1A$, $V_{GS} = 0V$			-1.15	V

■ Marking

Marking	3415
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